

Beam monitor online system design

BMOS readout design and DAQ plan

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Introduction

This work presents a beam monitor online system design for the 1.6 GeV proton beam at China Spallation Neutron Source (CSNS), based on silicon carbide (SiC) PIN sensors. Key aspects of the design include:

- Halo detection strategy: Detectors are placed outside the direct beam path $(2 \times 2 \text{ cm}^2 \text{ core})$ to monitor particles at beam edge, minimizing damage of beam while reconstructing beam parameters.
- Readout Electronics: A charge-sensitive amplifier with CR-RC shaping circuit processes signals.

The system enables real-time monitoring of the instensity, position, and uniformity of the updgraded CSNS beam.

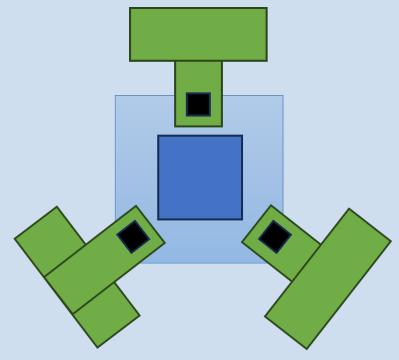
Design Objectives & Strategy

Key Objectives:

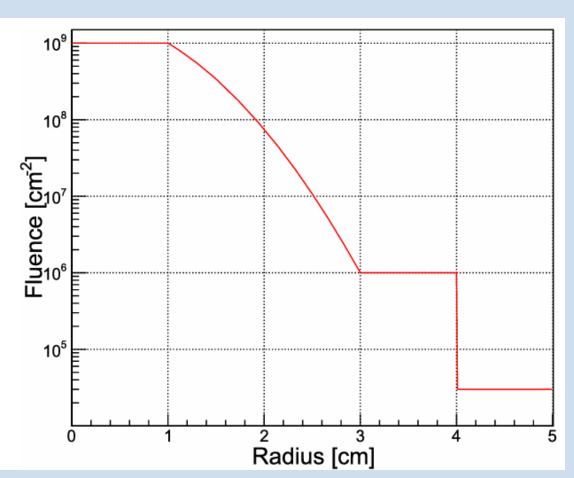
- Real-time Monitoring: Measure beam intensity, position, and uniformity with high precision
- **High Reliability:** Designed for 5,000+ hours/year continuous operation

Innovative Halo detection strategy:

- Beam Center: 2×2 cm² central zone
- Peripheral Detection: SiC detectors placed outside direct beam path
- **Key Advantage:** Monitors particles at beam edge to reconstruct beam parameters while avoiding direct damage of beam



The layout of BMOS detector. It consists of 3 movable detector boards around the beam center



The relationship between radius and fluence

Sensor Features:

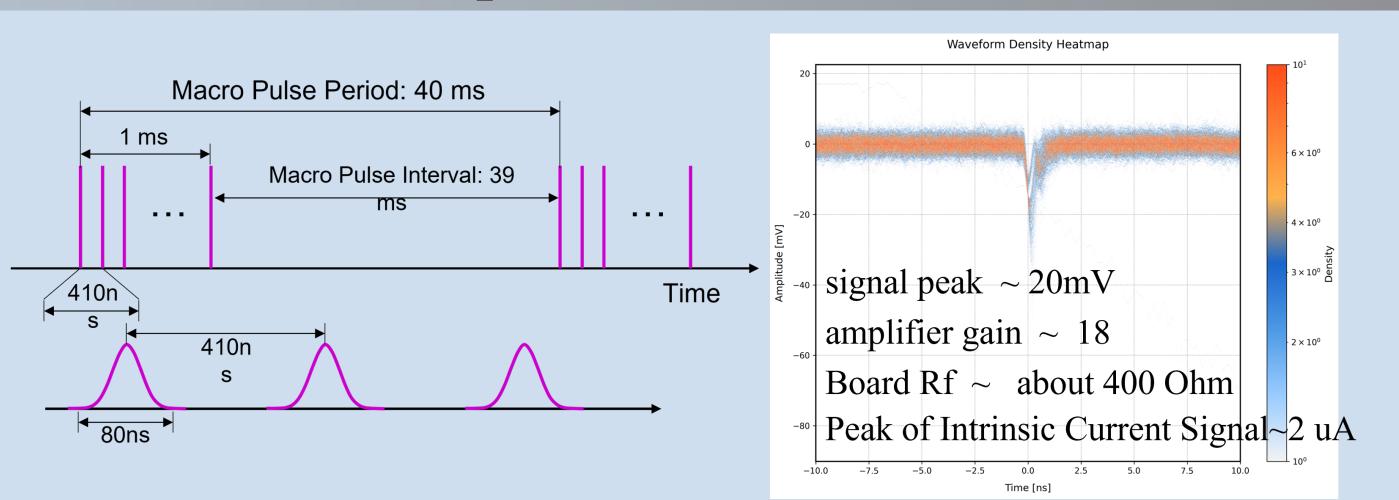
- 1. Radiation Hardness: 4H-SiC's wide bandgap and high atomic displacement threshold ensure stable operation in high-radiation environments
- 2. Thermal Performance: High thermal conductivity enables reliable room-temperature operation and effective heat dissipation

Beam Structure and Sensor Response

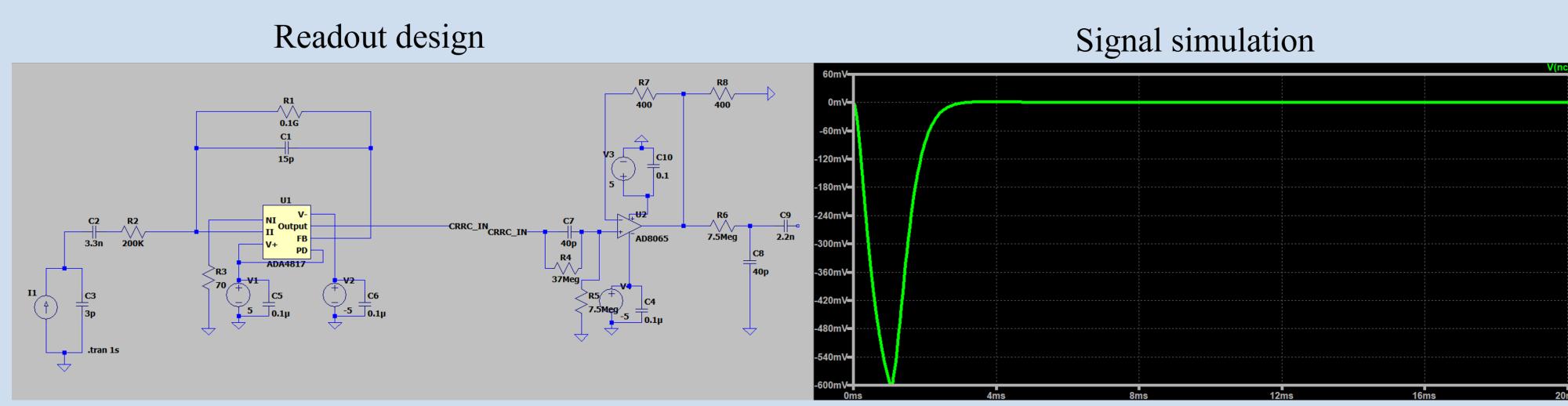
Macro Pulse Frequency: 25 Hz (24 Hz effective)

Macro Pulse Length: 1 ms, Interval: 39 ms Micro-pulse in macro-pulse

Micro-pulse period: 410 ns, Micro-pulse Length: 80 ns

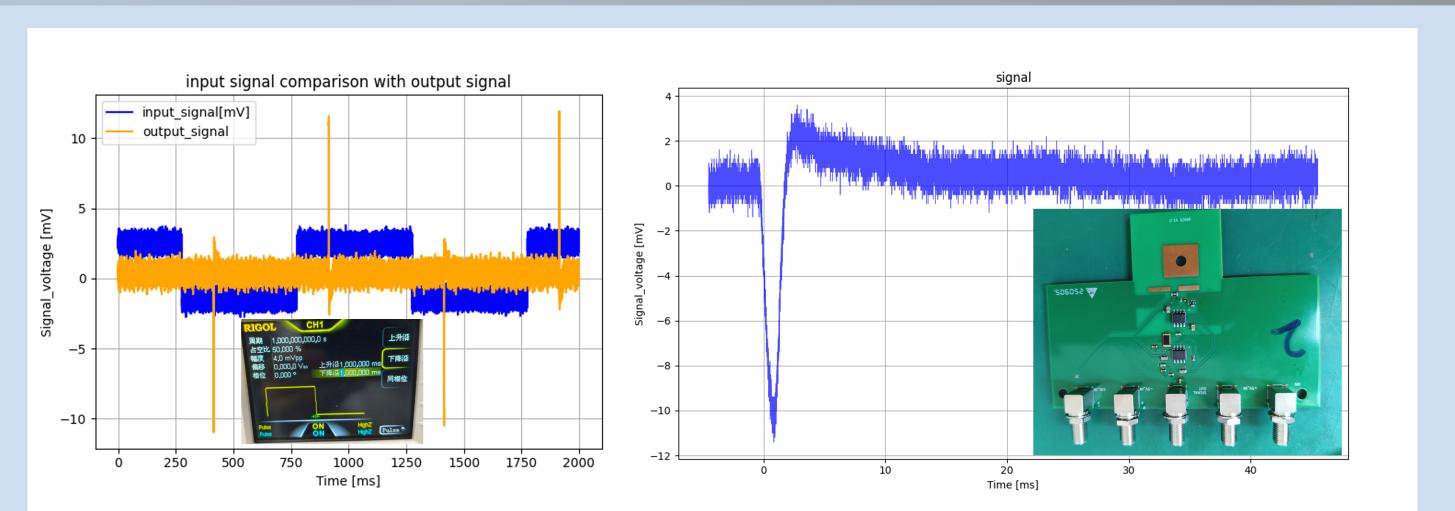


Total Read-out Design and Simulation



Charge-sensitive amplifier design with ADA4817 (Input resistance 500 GOhm, Open-Loop Gain 65 dB) (Integration capacitance 15 pF, Discharge time about 15 ms)

Measurement Result



Signals generated by the signal generator are injected into the circuit board through the cal-in port, and the output of the circuit board is observed

Future Work Plan

- Laser Testing: Validate circuit board response using laser-simulated detector signals and optimize signal processing algorithms.
- ADC/FPGA Development: Implement ADC and FPGA-based real-time beam intensity calculation.
- Vacuum Compatibility: Modify board materials and layout for vacuum chamber integration and conduct stability testing.

References

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- 2. Yang, T. et al. Time Resolution of the 4H-SiC PIN Detector. Front. Phys. 10, 718071 (2022).
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- 4. Zhao, S. et al. The study of 4H-SiC LGAD after proton radiation. arXiv:2507.12238 (2025).
- 5. Satapathy, Y. et al. Impact of Proton Irradiation on 4H-SiC Low Gain Avalanche Detectors (LGADs). arXiv:2507.23062 (2025).